

Customer No.: 31561  
Application No.: 10/710,405  
Docket No.: 13302-US-PA

### AMENDMENT

#### To the Claims:

1. (currently amended) A process of fabrication a semiconductor structure, comprising:  
providing a substrate;  
forming a dielectric layer over the substrate;  
forming a hydrophilic material layer over the dielectric layer, wherein residuals are formed on an edge of at least one of the substrate, the dielectric layer, the hydrophilic material layer or a combination thereof; and  
performing a polish process on the edge of at least one of the substrate, the dielectric layer, the hydrophilic material layer or a combination thereof to remove the residues; and  
forming a hardmask layer over the hydrophilic material layer.
- Claim 2. (canceled)
3. (currently amended) The process of claim ~~2~~ 1, wherein the ~~planarization~~ polish process comprises at least one of an upper bevel polish, a lower bevel polish, a side polish or a combination thereof.
4. (original) The process of claim 1, wherein a method of forming the dielectric layer comprises a spin on coating method or a chemical vapor deposition method.
5. (original) The process of claim 1, wherein a material of the dielectric layer comprises an organic dielectric material, a carbon-containing dielectric material or a carbon-containing oxide material.

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6. (original) The process of claim 1, wherein the dielectric layer is composed of at least a precursor comprising tetramethyl-cyclotetra-siloxane (TMCTS), trimethyl-silane (3MS), tetramethyl-silane (4MS), dimethyl-dimethoxy-silane (DMDMOS), octamethyl-cyclotetra-siloxane (OMCTS), diethoxy-methyl-silane (DEMS), or tetramethyl-disiloxane (TMDSO).

7. (original) The process of claim 1, wherein a material of the hydrophilic material layer comprises silane ( $\text{SiH}_4$ ) containing material, tetraethyl-ortho-silicate (TEOS) oxide containing material or silicon nitride.

8. (original) The process of claim 1, wherein a material of the hardmask layer comprises aluminum (Al), titanium nitride, tantalum nitride, titanium silicon nitride ( $\text{TiSiN}$ ), tungsten nitride, tungsten silicon nitride ( $\text{WSiN}$ ) or refractory nitride.

Claims 9-26 (canceled)

27. (new) A process of fabrication a semiconductor structure, comprising:

- providing a substrate;
- forming a first dielectric layer over the substrate;
- forming a first hydrophilic material layer over the first dielectric layer, wherein first residuals are formed on an edge of at least one of the substrate, the first dielectric layer, the first hydrophilic material layer or a combination thereof;
- performing a first polish process on the edge of at least one of the substrate, the first dielectric layer, the first hydrophilic material layer or a combination thereof to remove the first residues;

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forming a first hardmask layer over the first hydrophilic material layer;

forming a second dielectric layer over the first hardmask layer;

forming a second hydrophilic material layer over the second dielectric layer, wherein second first residuals are formed on an edge of at least one of the substrate, the first dielectric layer, the first hydrophilic material layer, the second dielectric layer, the second hydrophilic material layer or a combination thereof;

performing a second polish process on the edge of at least one of the substrate, the first dielectric layer, the first hydrophilic material layer, the second hydrophilic material layer or a combination thereof to remove the second residues; and

forming a second hardmask layer over the second hydrophilic material layer.

28. (new) The process of claim 27, wherein the first and second polish processes comprise at least one of an upper bevel polish, a lower bevel polish, a side polish or a combination thereof, respectively.

29. (new) The process of claim 27, wherein a method of forming the first and second dielectric layer comprises a spin on coating method or a chemical vapor deposition method.

30. (new) The process of claim 27, wherein the first and second dielectric layer comprise an organic dielectric material, a carbon-containing dielectric material or a carbon-containing oxide material, respectively.

31. (new) The process of claim 27, wherein the first and second dielectric layer are composed of at least a precursor comprising tetramethyl-cyclotetra-siloxane (TMCTS),

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trimethyl-silane (3MS), tetramethyl-silane (4MS), dimethyl-dimethoxy-silane (DMDMOS), octamethyl-cyclotetra-siloxane (OMCTS), diethoxy-methyl-silane (DEMS), or tetramethyl-disiloxane (TMDSO), respectively.

32. (new) The process of claim 27, wherein the first and second hydrophilic material layers comprise silane ( $\text{SiH}_4$ ) containing material, tetraethyl-ortho-silicate (TEOS) oxide containing material or silicon nitride, respectively.

33. (new) The process of claim 27, wherein the first and second hardmask layers comprise aluminum (Al), titanium nitride, tantalum nitride, titanium silicon nitride (TiSiN), tungsten nitride, tungsten silicon nitride (WSiN) or refractory nitride, respectively.

34. (new) The process of claim 27, further comprising forming a via in the first dielectric layer, the first hydrophilic layer and the first mask layer.

35. (new) the process of claim 34, further comprising forming a trench in the second dielectric layer, the second hydrophilic layer and the second mask layer, and the via is exposed within the trench.